



GBJ8005-GBJ810/G

Single Phase 8.0Amp Glass passivated Bridge Rectifiers

Features

- · Glass passivated die construction
- Low forward voltage drop
- High current capability
- High surge current capability
- Plastic material-UL flammability 94V-0
- The G suffix is uses for photoresist chip, otherwise it is a knife scraping chip

MECHANICAL DATA

- Case: Molded plastic, GBJ
- Terminals: Plated Leads Solderable perMIL-STD-202, Method 208
- Polarity: As Marked on Case
- Mounting Position: Any
- Marking: Type Number
- · Lead Free: For RoHS / Lead Free Version

Maximum Ratings And Electrical Characteristics (@T_A=25°C unless otherwise noted)

| | | | | | | 1 | | | | |
|------------------|---|-------------|-----|-----|-----|-----|-----------------------------|------|------|--|
| Symbol | Parameter | GBJ | GBJ | GBJ | GBJ | GBJ | GBJ | GBJ | Unit | |
| | | 8005 | 801 | 802 | 804 | 806 | 808 | 810 | | |
| V _{RRM} | repetitive peak reverse voltage | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | | |
| V _{RWM} | Working Peak Reverse Voltage | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V | |
| V _{RMS} | RMS voltage | 35 | 70 | 140 | 280 | 420 | 560 | 700 | - V | |
| V _{DC} | DC blocking voltage | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | | |
| IF _{AV} | Average Rectified Output | | | | | | | | A | |
| | Current (Note 2)@T _C =90°C | 8.0 | | | | | | | | |
| I _{FSM} | Peak forward surge current, 8.3ms single | 175 | | | | | | | А | |
| | half sine-wave | 175 | | | | | | | | |
| I ² | I ² _t Rating for fusing (t<8.3ms) | 127.09 | | | | | A _S ² | | | |
| V _{FM} | Forward Voltage @IF=4A | 1.0 1.10 | | | | | | V | | |
| | per element @IF=8A | | | | | | | | | |
| | Peak Reverse Current@T _A =25°C | 5.0 | | | | | | uA | | |
| Ι _R | at rated DC blocking voltage@ T _A =125°C | 500 | | | | | | | | |
| CJ | Typical junction capacitance | 55 | | | | | pF | | | |
| $R_{\theta JA}$ | Between junction and ambient, Without heatsink | 24 | | | | | °C/W | | | |
| R _{θJC} | Between junction and case, With heatsink | 1.6 | | | | | | | | |
| TJ | Operation Temperature Range | -55 to +150 | | | | | | °C | | |
| T _{STG} | Storage Temperature Range | -55 to +150 | | | | | | | | |
| | | | | | | | | | L | |

Note:(1)Thermal resistance from junction to case per element. Unit mounted on 75x75x1.6mm aluminum plate heat sink. BORN SEMICONDUCTOR , INC. ALL

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Mechanical Data





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Ratings And Characteristic Curves

Figure 1: Output Current Derating Curve

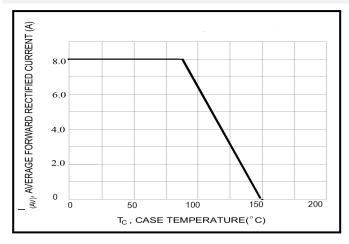


Figure 3:Maximum Peak Forward Surge Current (per

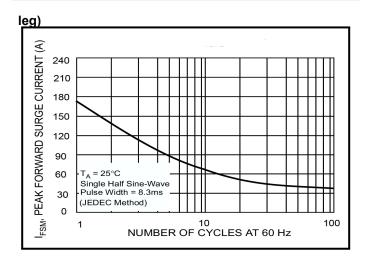
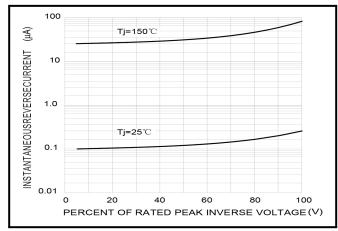


Figure 5:TYPICAL REVERSE CHARACTERISTICS



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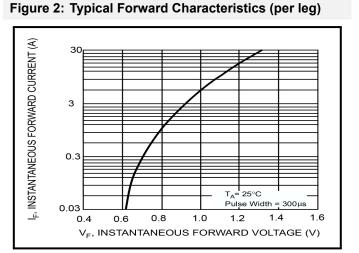
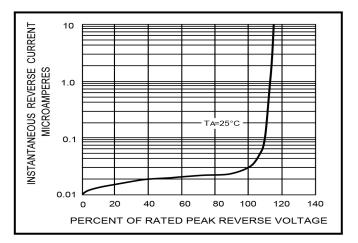


Figure 4: Typical Junction Capacitance





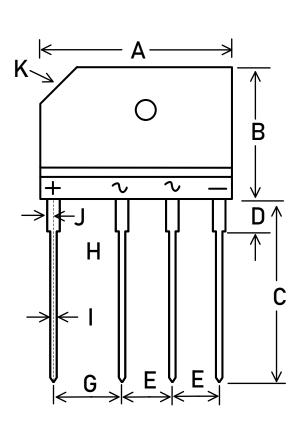


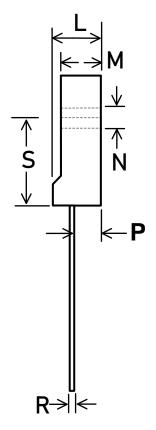


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Outline Drawing -GBJ





| OVMDOL | MILLIMETER | | | | | |
|--------|------------|-------|--|--|--|--|
| SYMBOL | MIN. | MAX. | | | | |
| A | 29.70 | 30.3 | | | | |
| В | 19.70 | 20.3 | | | | |
| С | 17.00 | 18.00 | | | | |
| D | 3.80 | 4.20 | | | | |
| E | 7.30 | 7.70 | | | | |
| G | 9.80 | 10.20 | | | | |
| Н | 2.00 | 2.40 | | | | |
| I | 0.90 | 1.10 | | | | |
| J | 2.30 | 2.70 | | | | |
| K | 3.0x | ۲45° | | | | |
| L | 4.40 | 4.80 | | | | |
| М | 3.40 | 3.80 | | | | |
| N | 3.10 | 3.40 | | | | |
| Р | 2.50 | 2.90 | | | | |
| R | 0.60 | 0.80 | | | | |
| S | 10.80 | 11.20 | | | | |

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Specifications are subject to change without notice. Please refer to http://www.born-tw.com for current information. Revision: 2022-Jan-1

